



IOCN 2020

Enhanced Efficiency of Inverted Perovskite Solar Cells by Passivating Hole Transport Layer with POSS

Department of Chemical and Materials Engineering, National Yunlin University of Science and Technology

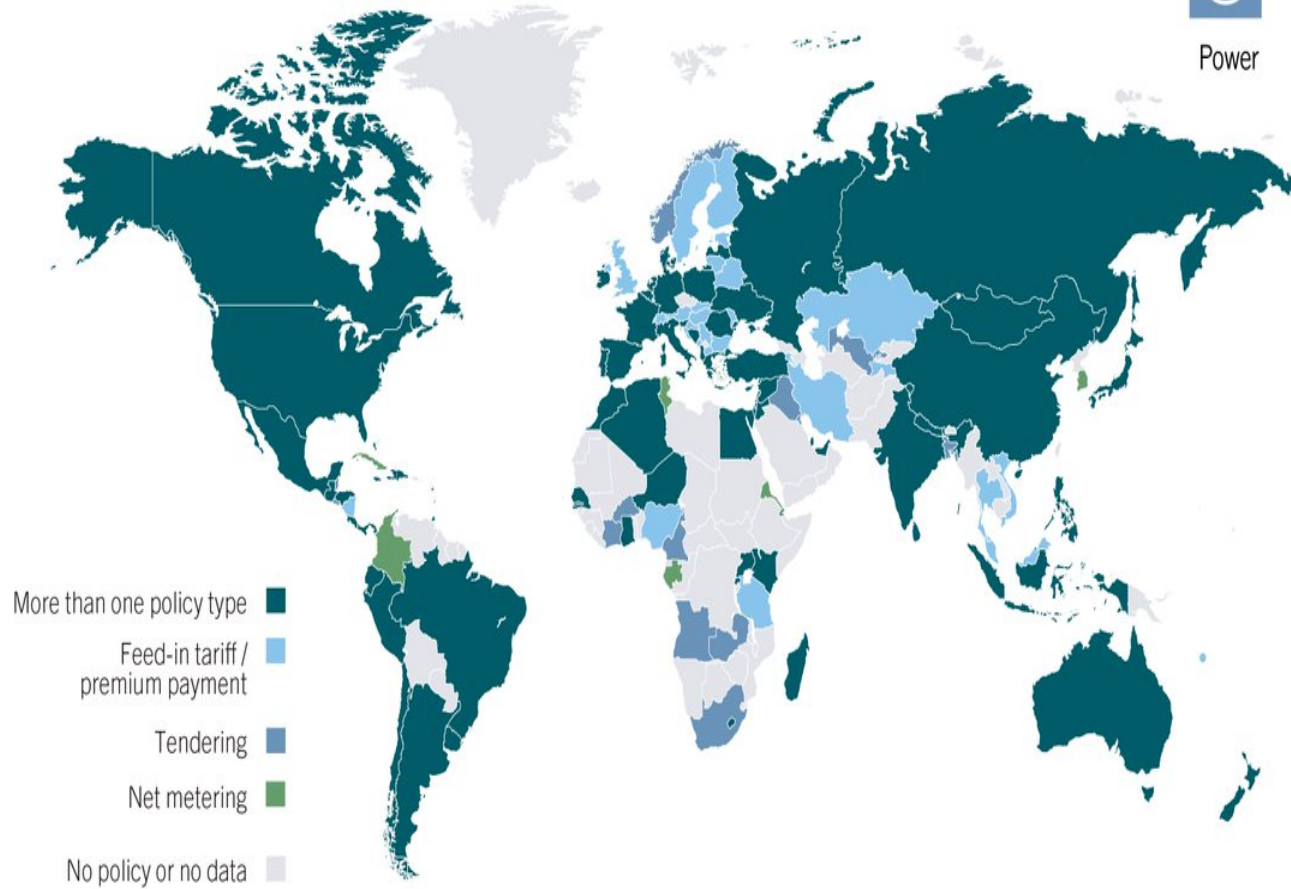
Bo-Tau Liu, Hong-Ru Lin

15-30 NOV. 2020

Countries with Renewable Energy Power Policies, by Type, 2015



Power



Note: Countries are considered to have policies when at least one national or state/provincial-level policy is in place.

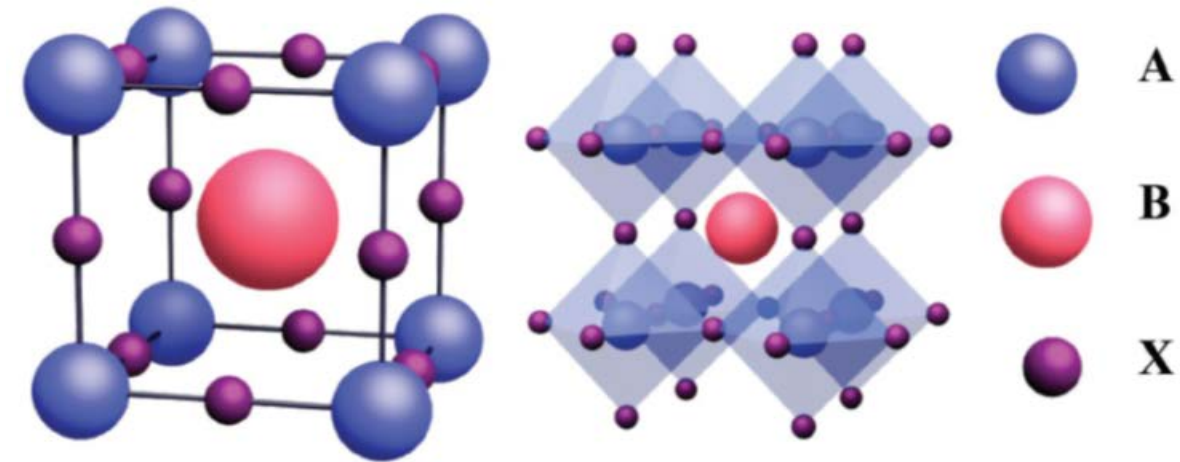
REN21 *Renewables 2016 Global Status Report*



Source: REN21 Policy Database



ABX₃



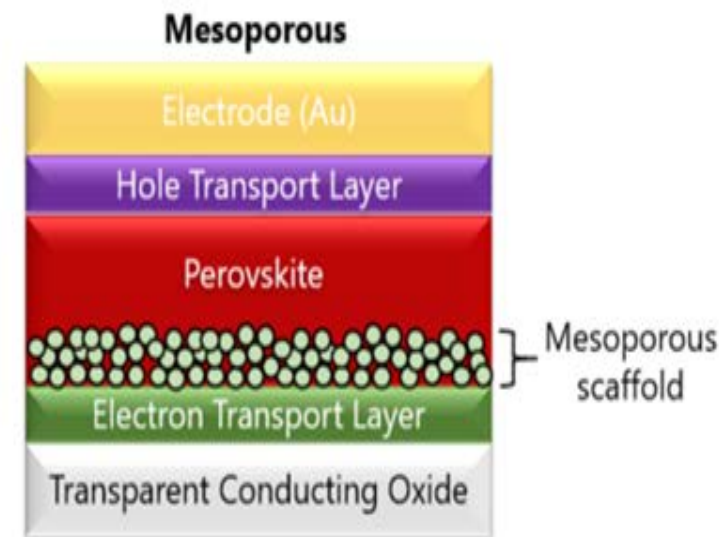
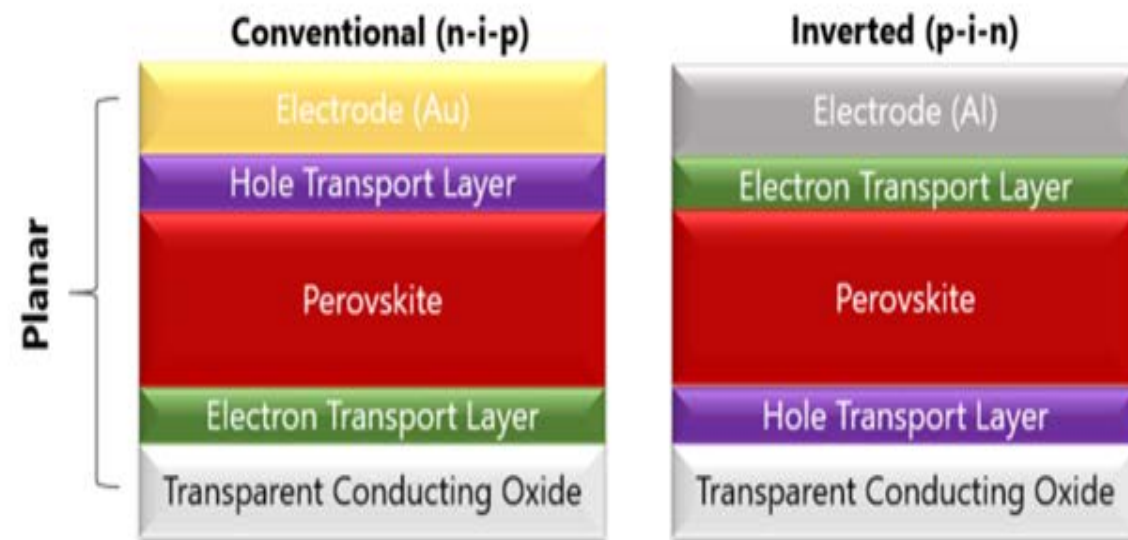
A: Na⁺、K⁺、Ca²⁺、Sr²⁺、Pb²⁺、Ba²⁺

B: Ti⁴⁺、Cd²⁺、Nb⁵⁺、Mn⁶⁺、Fe³⁺、Zr⁴⁺

X: O²⁻、F⁻、Cl⁻、Br⁻、I⁻

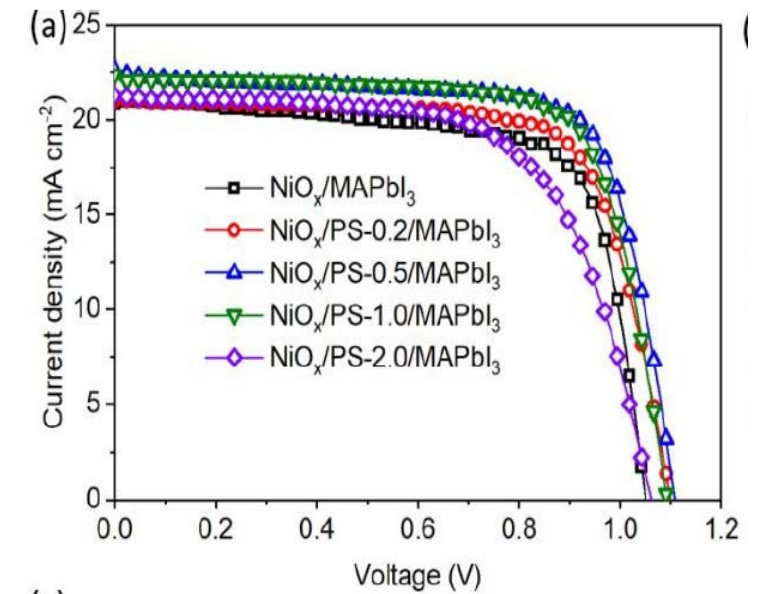
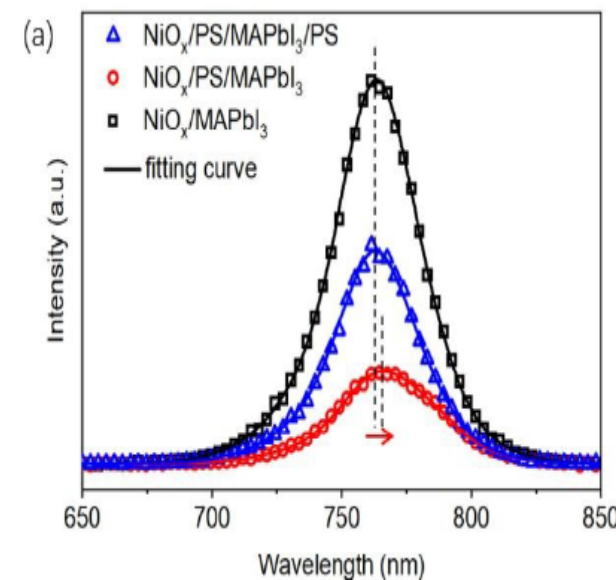
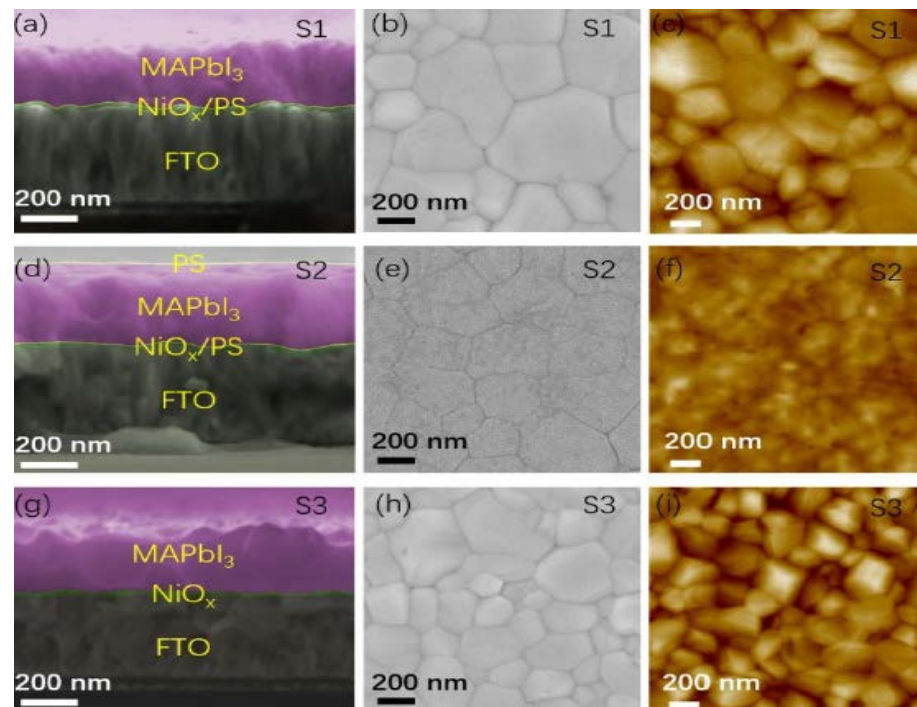
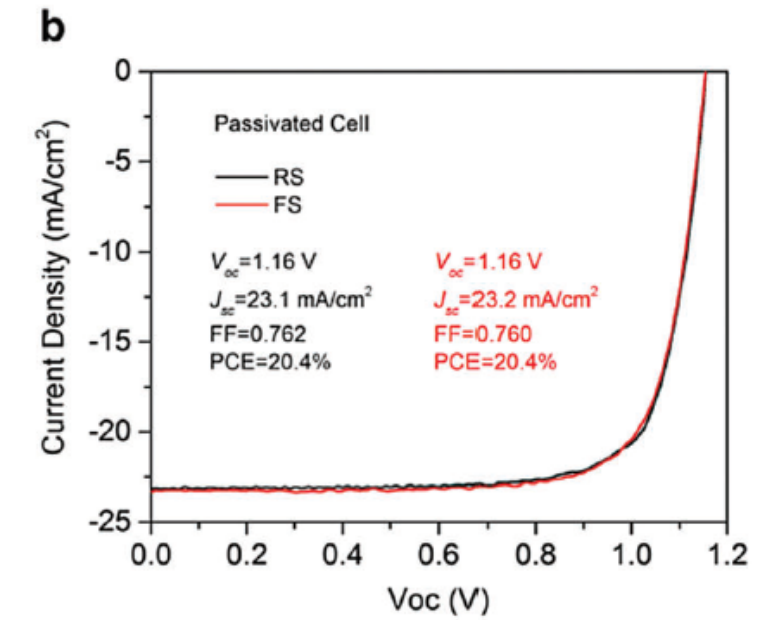
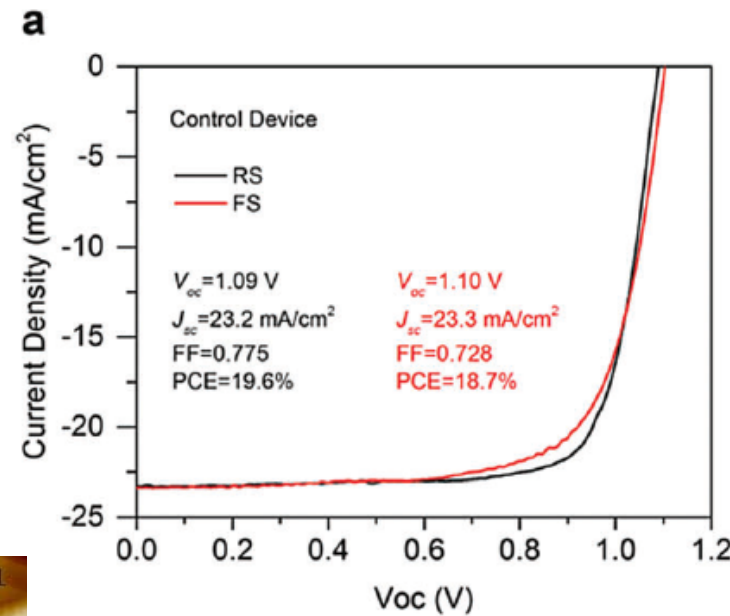
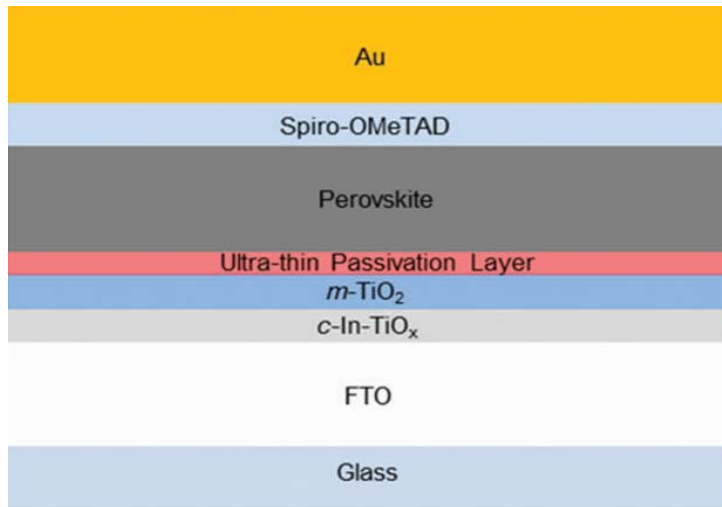
CH₃NH₃PbI₃ is one of the most used perovskite materials

Common Structure



Interface passivation

Energy Environ. Sci. 2017, 10, 1792
 J. Mater. Chem. A 2019, 7, 21730





NiO_x Synthesis

Ethylenediamine (EDA)
EDA:Ni⁺=1: $\frac{2}{3}$ *molar ratio*



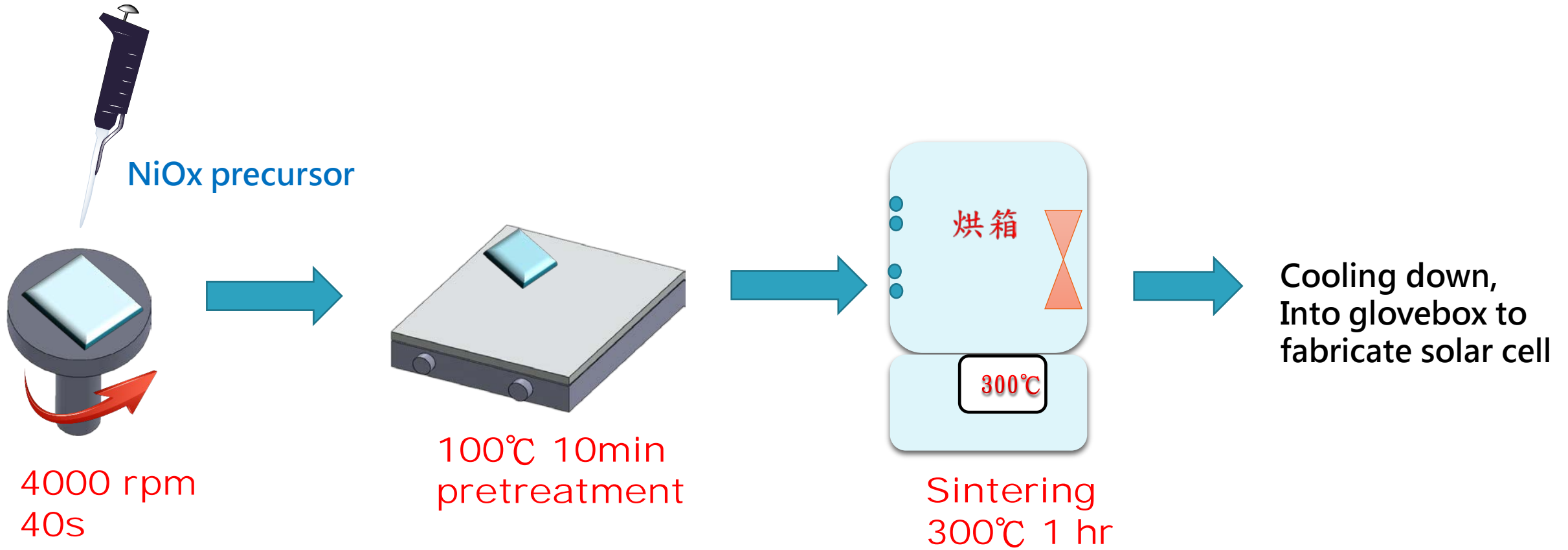
On hotplate stirring
overnight keep at 60 °C

0.6M Nickel(II)
nitrate(99.9985%, Alfa Aesar)
2-Methoxyethanol Sol.

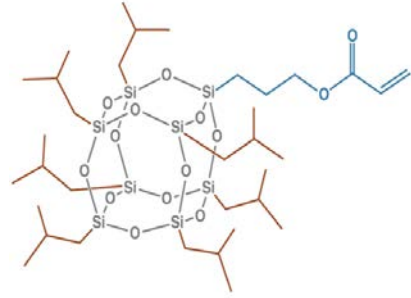
NiO_x precursor

| | Boiling point |
|------------------|---------------|
| ethylene glycol | 197.3 °C |
| 2-Methoxyethanol | 124-125°C |

High Voltage NiO_x Synthesis

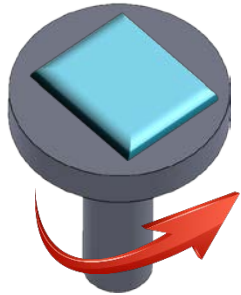
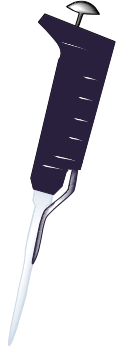


Device Fabrication



MA0701 POSS
different conc.

(W.O. 、 0.005 、 0.01 、
0.015 、 0.05 mg/ml
IPA Sol.)



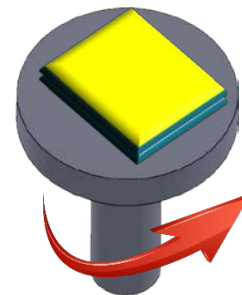
6000 rpm
20s

Annealing

100°C
10 Min



MAPbI₃ 1.45M
DMF : DMSO=4:1

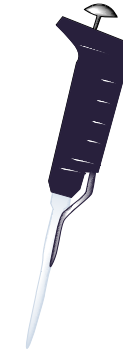


4000 rpm
25s

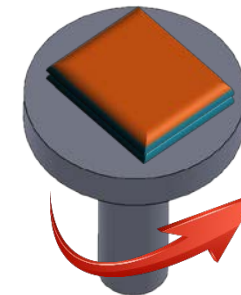
Annealing

100°C
10 Min

Added Anisole as
antisolvent within 10s

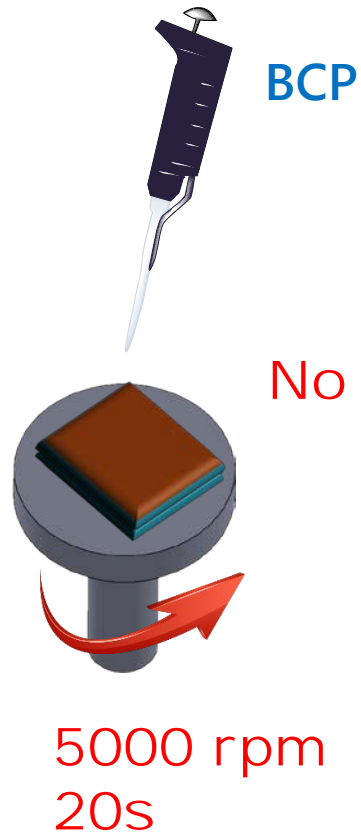


PC₆₁BM

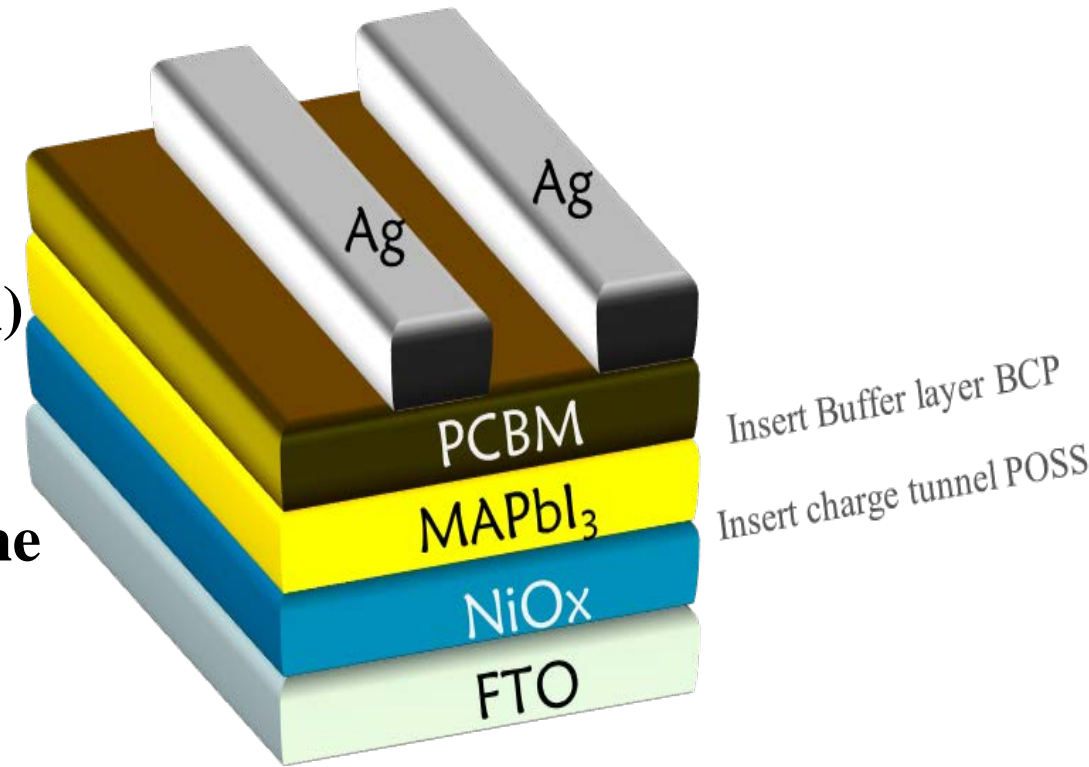


3000 rpm
20s

Device Fabrication

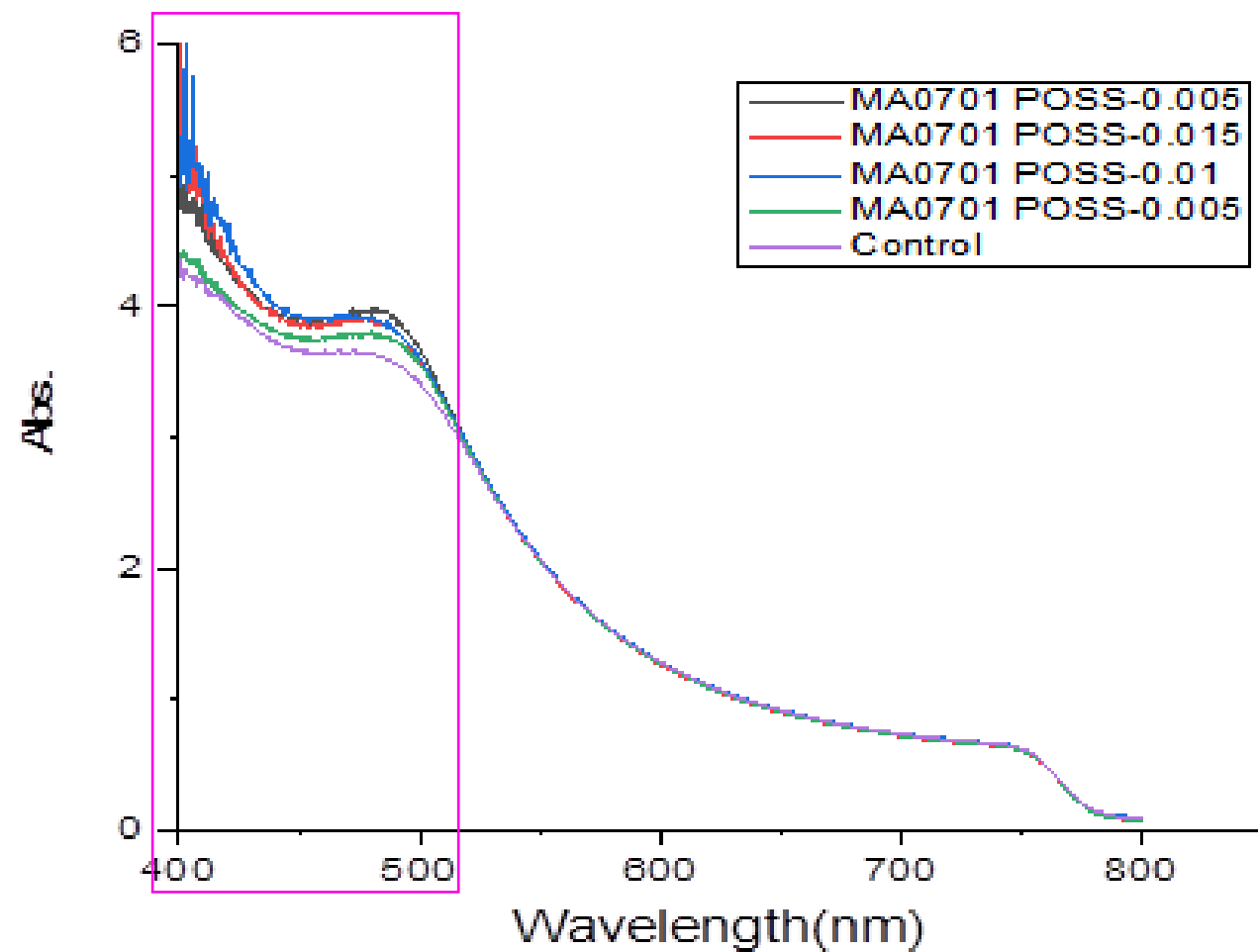
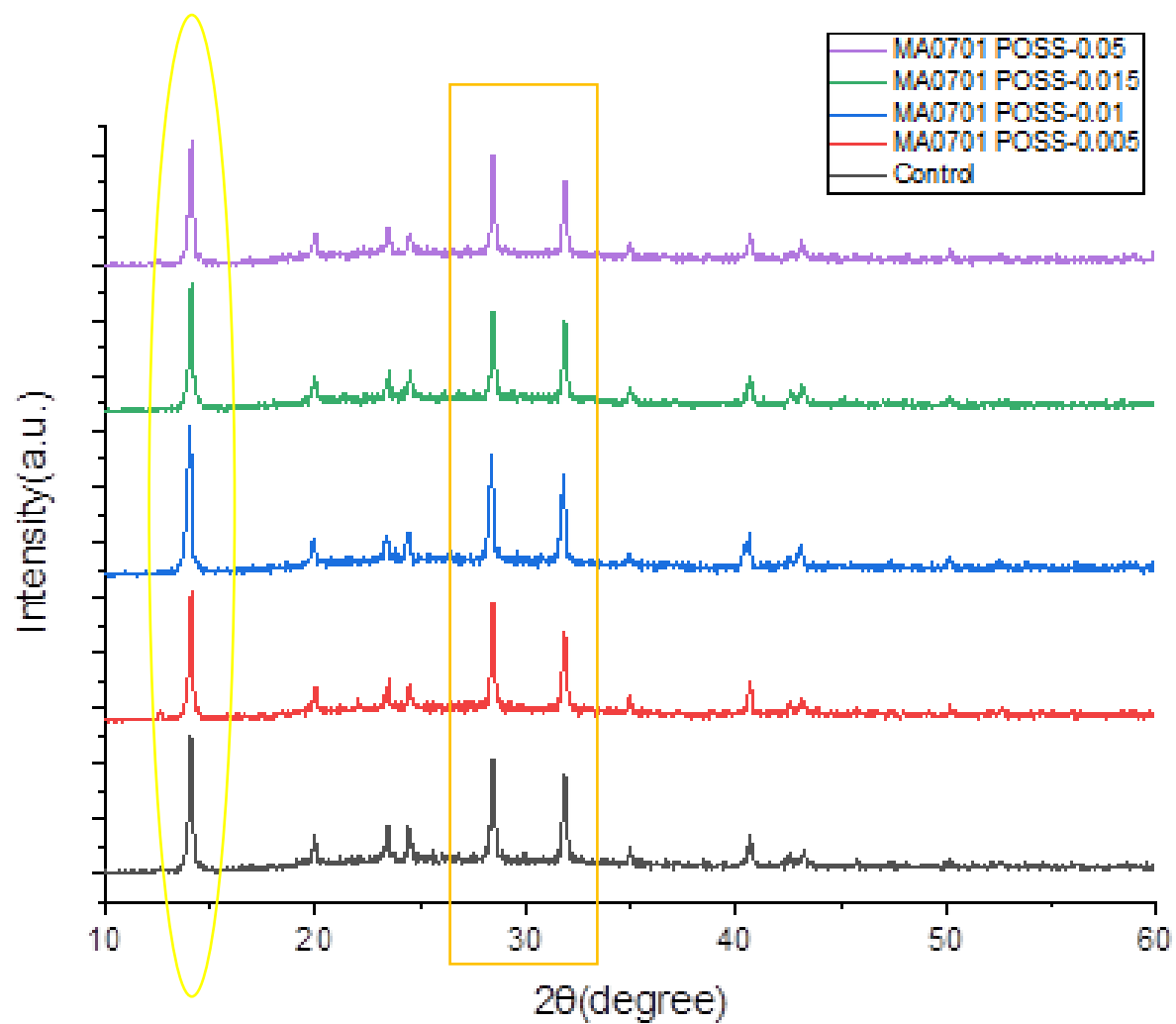


an Ag electrode (~ 100 nm) was thermally deposited under a base pressure of $\sim 2 \times 10^{-4}$ Pa to complete the device.

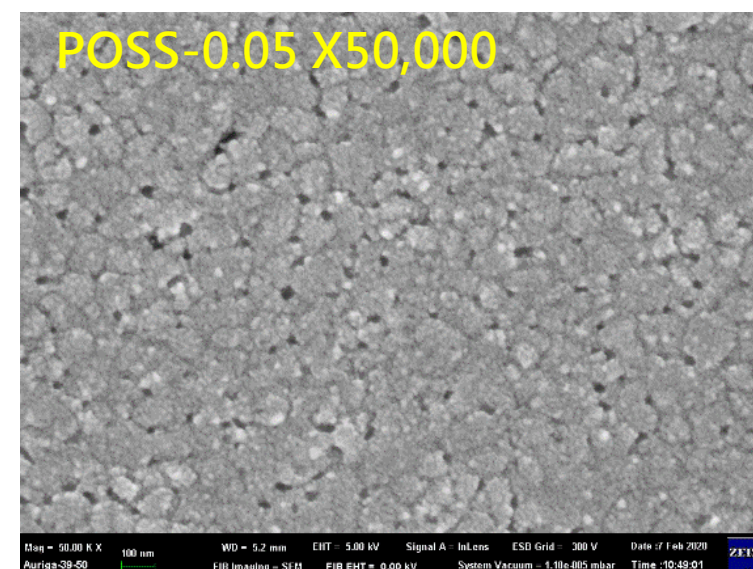
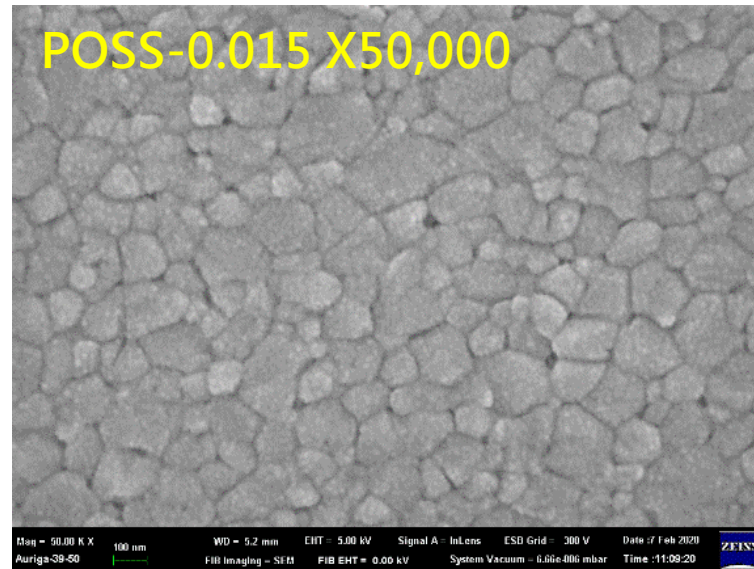
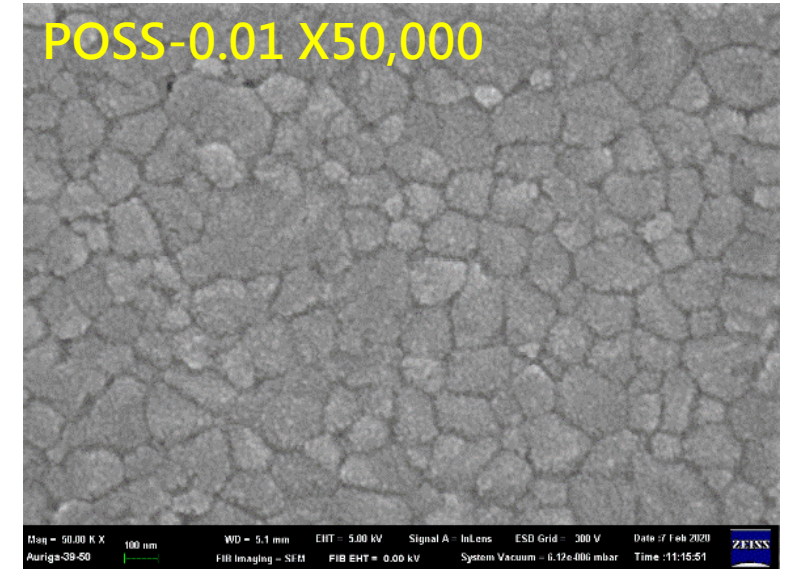
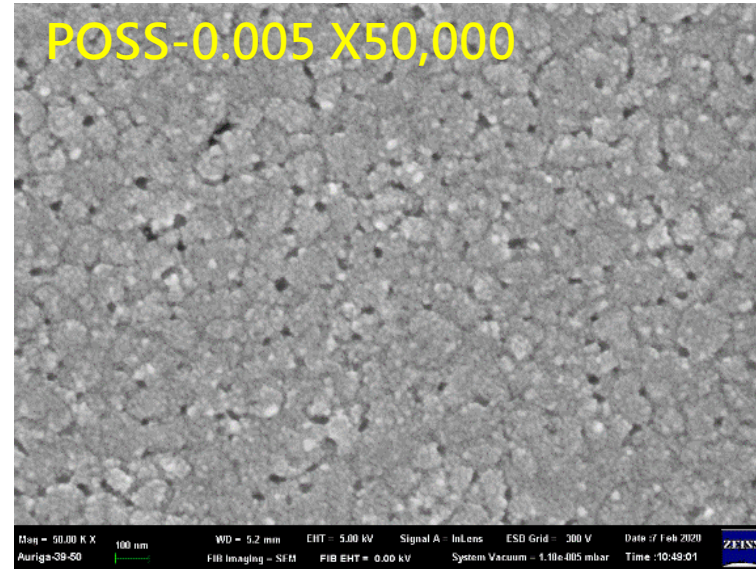
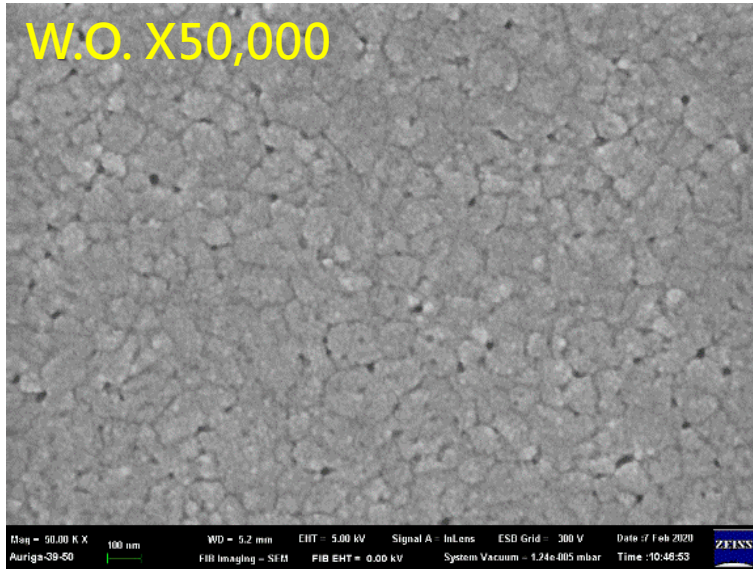




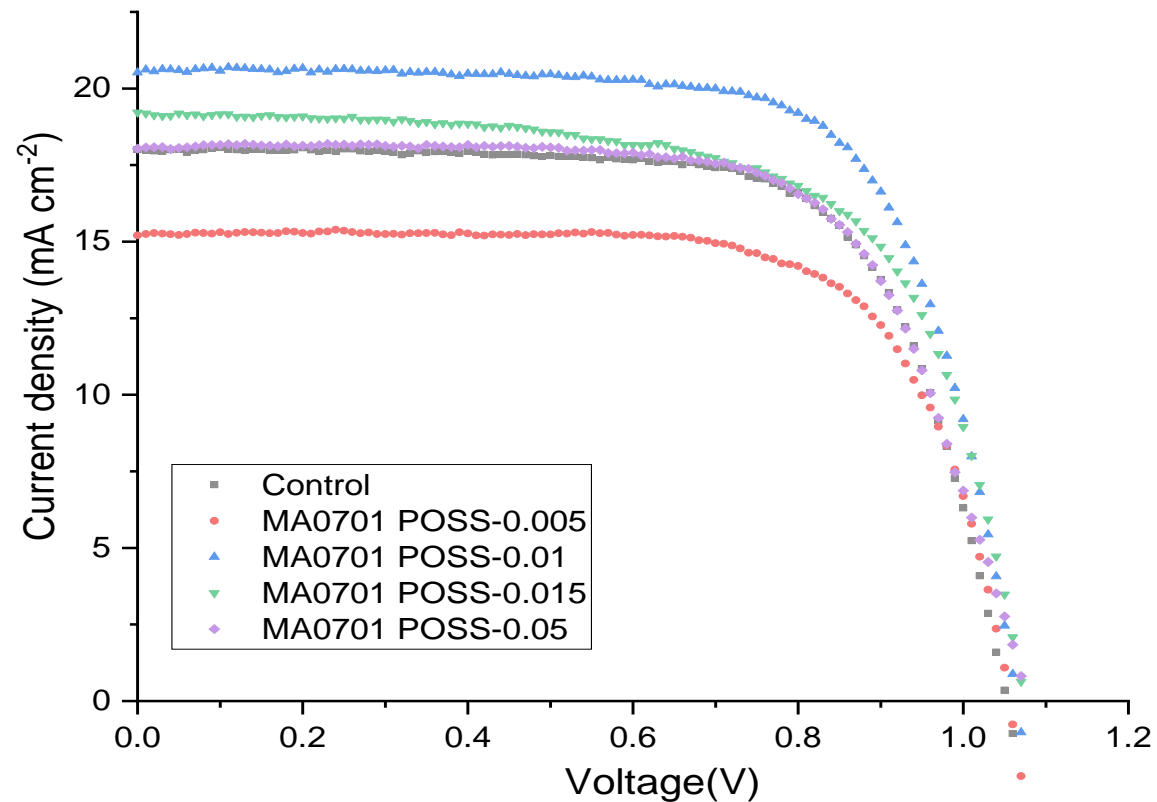
XRD & UV-Vis



MA0701 POSS/ NiOx SEM images

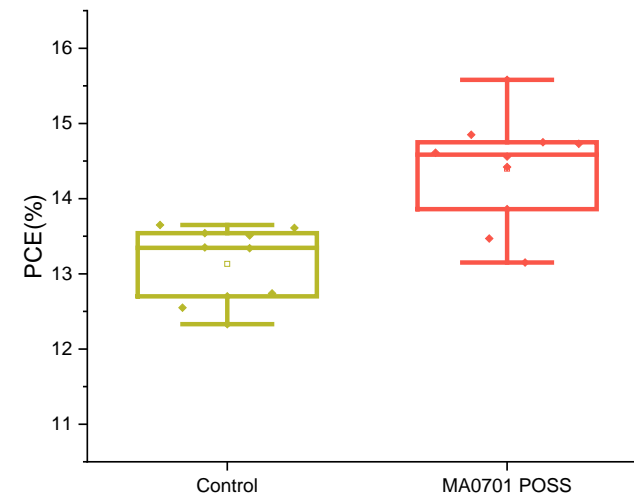
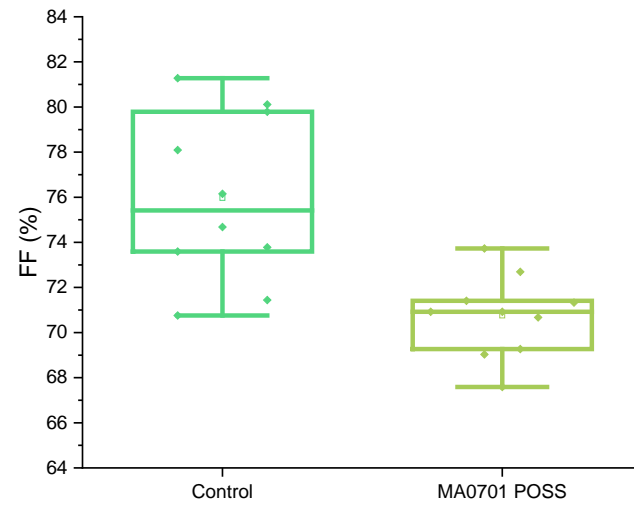
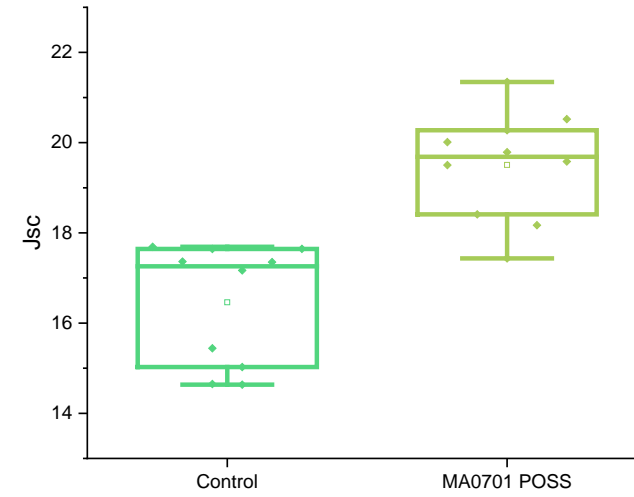
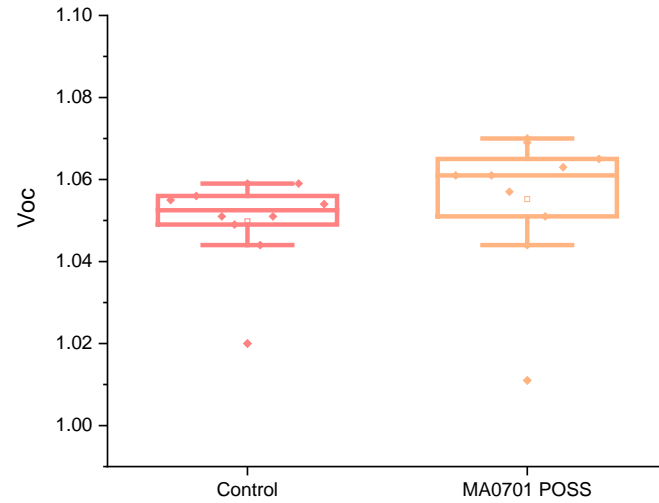
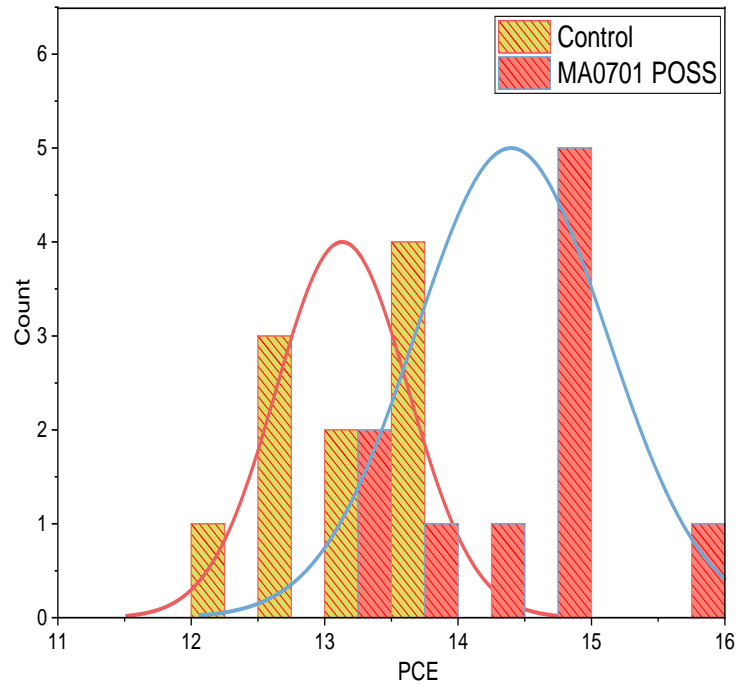


Effect of POSS on J-V curve



| Sample | Voc [volt] | Jsc [mA cm ⁻²] | FF [%] | Average PCE [%] [Best] |
|------------|------------|----------------------------|--------|--------------------------|
| Control | 1.053 | 18.004 | 70.18 | 12.55±0.49 [13.30] |
| POSS-0.005 | 1.048 | 18.391 | 73.78 | 12.64±1.23 [14.14] |
| POSS-0.01 | 1.065 | 20.521 | 71.33 | 14.75±0.71 [15.58] |
| POSS-0.015 | 1.074 | 19.222 | 66.16 | 12.85±0.35 [13.66] |
| POSS-0.05 | 1.056 | 15.206 | 71.60 | 10.91±0.62 [11.50] |

Effect of POSS on photovoltaic properties



Conclusions

- In this study, we are the first to attempt to use POSS to passivate NO_x . The PSCs with fluorine-doped tin oxide (FTO)/ NO_x /POSS/MAPbI₃/PC₆₁BM/Bathocuproine (BCP)/Ag structure were fabricated.
- The result showed that the POSS passivation improved significantly crystal size of perovskite, short circuit current (J_{SC}), and PCE.
- At 0.01-wt% POSS, the PCE increase from 13.3 to 15.58%, an enhancement of 17%. This enhancement was mainly due to the increase of the J_{SC} from 18.0 to 20.5 mA/cm², an increase of 13%.



THANKS
FOR YOUR LISTENING!